

## ABSTRACT

Disclosed is a method for forming conducting wire and contact opening in a  
5 semiconductor device. The method comprises steps of providing a substrate; forming a first  
dielectric layer on the substrate; digging a via in the first dielectric layer and filling metal  
therein; forming a conductor layer on the first dielectric including the via; forming a metal  
layer on the conductor layer; removing unnecessary portions of the conductor/metal layers to  
define recesses, with the left portions to form conducting wires; applying a second dielectric  
10 layer to fill the recesses and performing planarization thereto to expose the conducting wires;  
forming a third dielectric layer; forming photoresist of predetermined pattern on the third  
dielectric layer; removing predetermined portion of the third dielectric layer to form a contact  
opening; and removing the photoresist.